

100V Trench MOS Barrier Schottky

Ultra Low VF 0.57V@15A, 25 °C

Features

- Trench MOS schottky technology
- Low stored charge Majority Carrier Conduction
- Ultra low forward voltage drop
- Low leakage current
- Low power loss and high efficiency
- High surge capacity
- ESD rating:>20K volts

Typical Application

Schottky rectifier design for high frequency switched mode power supplies, such as adaptators and on board DC/DC converters.

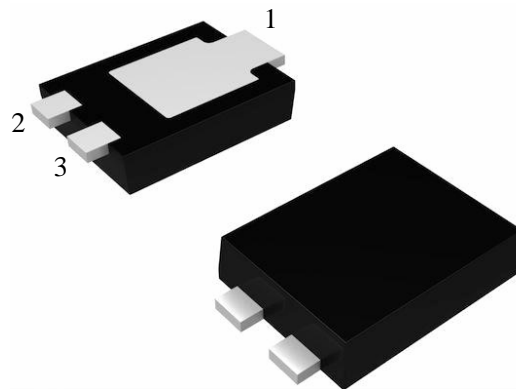
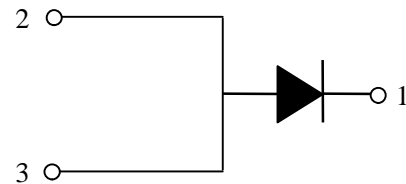
Mechanical Data

Case: JEDEC TO-277 , molded plastic body

Terminals: Plated leads, solderable per MIL-STD-750, Method 2026

Mounting Position: Any

15 Amperes, 100 Volts



TO-277

Device Summary

Symbol	Value
$I_F(AV)$	15 A
V_{RRM}	100V
$V_F(Typical)$	0.57V
$T_j(max)$	150 °C

Note: Pins 2 & 3 must be electrically connected at the printed circuit board.

Major Rating and Characteristics(per diode)				
Symbol	Parameter		Values	Units
V_{RRM}	Repetitive peak reverse voltage		100	V
T_J	Storage temperature range		-55 to 150	$^{\circ}C$
I_{FSM}	Surge non repetitive forward current	10 ms sine or 6 ms rect. pulse	350	A
$I_{F(AV)}$	Maximum average forward current 50 % duty cycle, rectangular waveform		$T_C=25^{\circ}C$ 15	

Electrical Characteristics($T_A=25^{\circ}C$ unless otherwise noted)						
Parameter	Test condition		Symbol	TYP	MAX	UNITS
Forward Voltage drop	$I_F=5A$	$T_A=25^{\circ}C$	$V_F^{(1)}$	0.45	-	V
	$I_F=10A$			0.51		
	$I_F=15A$			0.57	0.65	
	$I_F=5A$	$T_A=125^{\circ}C$		0.41	-	
	$I_F=10A$			0.56		
	$I_F=15A$			0.52	0.60	
Reverse leakage current	$V_R=100V$	$T_A=25^{\circ}C$	$I_R^{(2)}$	-	50	μA
		$T_A=125^{\circ}C$		15	70	mA
Junction capacitance	$V_R=5V_{DC}, 25^{\circ}C(1MHz)$		C_j	1000		pF

Notes (1) Pulse test: 300us pulse width,2% duty cycle (2) Pulse test: 300us pulse width,2% duty cycle

Thermal Characteristics($T_A=25^{\circ}C$ unless otherwise noted)			
Parameter	Symbol	SK15U100AAPU	UNIT
Typical thermal resistance	$R_{JA}^{(1)}$	75	$^{\circ}C/W$
	$R_{JM}^{(2)}$	34	

Notes

(1) Free air, mounted on recommended PCB, 2oz.pad area; thermal resistance R_{JA} -junction to ambient

(2) Cathode pad dimensions 18.8mm x 14.4mm. Anode pad dimensions 5.6mm x 14.4mm;

R_{JM} -junction to mount

Characteristics Curves ($T_A=25\text{ }^\circ\text{C}$ unless otherwise noted)

Fig.1 Typical Forward Voltage Characteristics

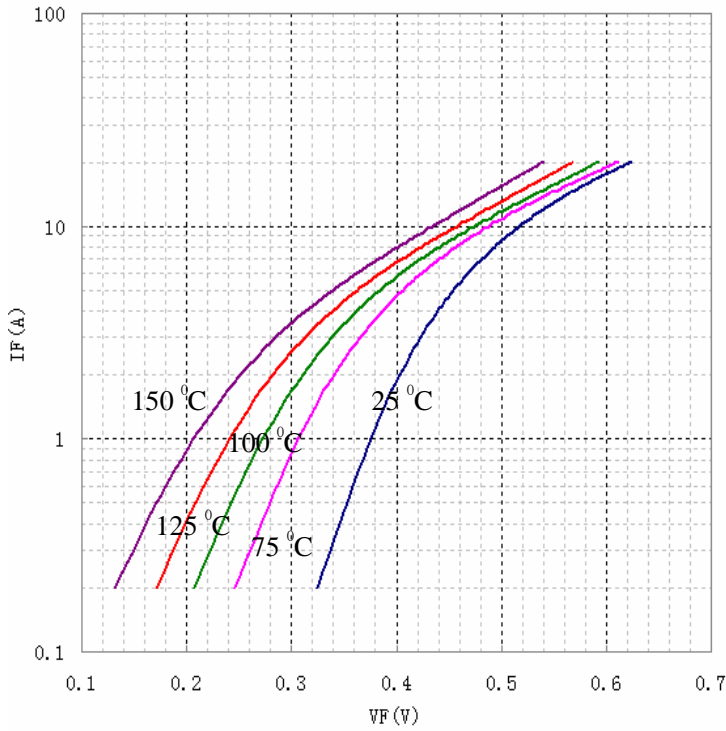
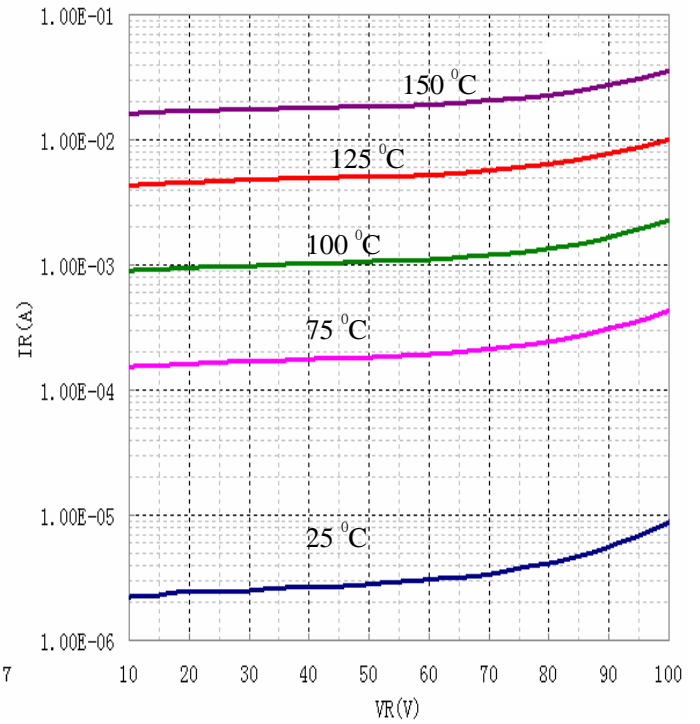


Fig.2 Typical Reverse Leakage Characteristics



Package Outline Dimensions in Millimeters

